



Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known			
		Application Number	10/801,499		
		Filing Date	March 15, 2004		
		First Named Inventor	Calafut, Daniel		
		Art Unit	Not Yet Assigned		
		Examiner Name	Not Yet Assigned		
Sheet	1	of	11	Attorney Docket Number	018865-015200US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
A. U	AA	US-3,404,295	10-01-1968	Warner et al.	
	AB	US-3,412,297	11-19-1968	Amlinger	
	AC	US-3,497,777	02-24-1970	Teszner et al.	
	AD	US-3,564,356	02-16-1971	Wilson	
	AE	US-4,003,072	01-11-1977	Matsushita et al.	
	AF	US-4,300,150	11-10-1981	Colak	
	AG	US-4,326,332	04-27-1982	Kenney et al.	
	AH	US-4,337,474	06-29-1982	Yukimoto	
	AI	US-4,579,621	04-01-1986	Hine	
	AJ	US-4,636,281	01-13-1987	Buiguez et al.	
	AK	US-4,638,344	01-20-1987	Cardwell, Jr.	
	AL	US-4,639,761	01-27-1987	Singer et al.	
	AM	US-4,698,653	10-06-1987	Cardwell, Jr.	
	AN	US-4,716,126	12-29-1987	Cogan	
	AO	US-4,746,630	05-24-1988	Hui et al.	
	AP	US-4,754,310	06-28-1988	Coe	
	AQ	US-4,774,556	09-27-1988	Fujii et al.	
	AR	US-4,801,986	01-31-1989	Chang et al.	
	AS	US-4,821,095	04-11-1989	Temple	
	AT	US-4,823,176	04-18-1989	Baliga et al.	
	AU	US-4,853,345	08-01-1989	Himelick	
	AV	US-4,868,624	09-19-1989	Grung et al.	
	AW	US-4,893,160	01-09-1990	Blanchard	
	AX	US-4,914,058	04-03-1990	Blanchard	
	AY	US-4,941,026	07-10-1990	Temple	
	AZ	US-4,967,245	10-30-1990	Cogan et al.	
	BA	US-4,974,059	11-27-1990	Kinzer	
	BB	US-4,990,463	02-05-1991	Mori	
	BC	US-4,992,390	02-12-1991	Hsueh-Rong Chang	
	BD	US-5,027,180	06-25-1991	Nishizawa et al.	
	BE	US-5,071,782	12-10-1991	Mori	
	BF	US-5,072,266	12-10-1991	Buluccea	
	BG	US-5,079,608	01-07-1992	Wodarczyk et al.	
	BH	US-5,105,243	04-14-1992	Nakagawa et al.	
	BI	US 5,111,253	05-05-1992	Korman et al.	
	BJ	US-5,142,640	08-25-1992	Iwanatsu	
	BK	US-5,164,325	11-17-1992	Cogan et al.	
	BL	US-5,164,802	11-17-1992	Jones et al.	
	BM	US-5,216,275	06-01-1993	Chen	
	BN	US-5,219,777	06-15-1993	Kang	

Examiner Signature	ANH D. MA	Date Considered	10/17/2005
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U.S. PATENT DOCUMENTS+					
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		Number Kind Code ² (if known)			
A.M.	BO	US-5,219,793	06-15-1993	Cooper et al.	
	BP	US-5,233,215	08-03-1993	Baliga	
	BQ	US-5,262,336	11-16-1993	Pike, Jr. et al.	
	BR	US-5,268,311	12-07-1993	Euen et al.	
	BS	US-5,275,965	01-04-1994	Manning	
	BT	US-5,294,824	03-15-1994	Okada	
	BU	US-5,298,761	03-29-1994	Cogan et al.	
	BV	US-5,300,447	04-05-1994	Anderson	
	BW	US-5,326,711	07-05-1994	Maihi	
	BX	US-5,350,937	09-27-1994	Yamazaki et al.	
	BY	US-5,365,102	11-15-1994	Mehrotra et al.	
	BZ	US-5,366,914	11-22-1994	Takahashi et al.	
	CA	US-5,389,815	02-14-1995	Takahashi	
	CB	US-5,405,794	04-11-1995	Kim	
	CC	US-5,418,376	05-23-1995	Muraoka et al.	
	CD	US-5,424,231	06-13-1995	Yang	
	CE	US-5,429,977	07-04-1995	Lu et al.	
	CF	US-5,430,311	07-04-1995	Murakami et al.	
	CG	US-5,430,324	07-04-1995	Bencuya	
	CH	US-5,436,189	07-25-1995	Beasom	
	CI	US-5,438,215	08-01-1995	Tihanyi	
	CJ	US-5,442,214	08-15-1995	Yang	
	CK	US-5,454,435	07-18-1995	Baliga	
	CL	US-5,473,176	12-05-1995	Kakumoto	
	CM	US-5,473,180	12-05-1995	Ludikhuize	
	CN	US-5,474,943	12-12-1995	Hshieh et al.	
	CO	US-5,519,245	05-21-1996	Tokura et al.	
	CP	US-5,541,425	07-30-1996	Nishihara	
	CQ	US-5,554,862	09-10-1996	Omura et al.	
	CR	US-5,567,634	10-22-1996	Hebert et al.	
	CS	US-5,567,635	10-22-1996	Acovic et al.	
	CT	US-5,572,048	11-05-1996	Sugawara	
	CU	US-5,576,245	11-19-1996	Cogan et al.	
	CV	US-5,578,851	11-26-1996	Hshieh et al.	
	CW	US-5,581,100	12-03-1996	Ajit	
	CX	US-5,583,065	12-10-1996	Miwa	
	CY	US-5,592,005	01-07-1997	Floyd et al.	
	CZ	US-5,595,927	01-21-1997	Chen et al.	
	DA	US-5,597,765	01-28-1997	Yilmaz et al.	
	DB	US-5,605,852	02-25-1997	Bencuya	

Examiner Signature	ANTH D. UAI	Date Considered	10/17/2005
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		Number Kind Code ² (if known)			
A. M.	DC	US-5,623,152	04-22-1997	Majumdar et al.	
	DD	US-5,629,543	05-13-1997	Hshieh et al.	
	DE	US-5,637,898	06-10-1997	Baliga	
	DF	US-5,639,676	06-17-1997	Hshieh et al.	
	DG	US-5,640,034	07-17-1997	Satwinder Malhi	
	DH	US-5,648,670	07-15-1997	Blanchard	
	DI	US-5,656,843	08-12-1997	Goodyear et al.	
	DJ	US-5,665,619	09-09-1997	Kwan et al.	
	DK	US-5,670,803	09-23-1997	Beilstein, Jr. et al.	
	DL	US-5,689,128	11-18-1997	Hshieh et al.	
	DM	US-5,693,569	12-02-1997	Ueno	
	DN	US-5,705,409	01-06-1998	Witek	
	DO	US-5,710,072	01-20-1998	Krautschneider et al.	
	DP	US-5,714,781	02-03-1998	Yamamoto et al.	
	DQ	US-5,719,409	02-17-1998	Singh et al.	
	DR	US-5,770,878	06-23-1998	Beasom	
	DS	US-5,776,813	07-07-1998	Huang et al.	
	DT	US-5,780,343	07-14-1998	Bashir	
	DU	US-5,801,417	09-01-1998	Tsang et al.	
	DV	US-5,877,528	03-02-1999	So	
	DW	US-5,879,971	03-09-1999	Witek	
	DX	US-5,879,994	03-09-1999	Kwan et al.	
	DY	US-5,895,951	04-20-1999	So et al.	
	DZ	US-5,895,952	04-20-1999	Darwish et al.	
	EA	US-5,897,343	04-27-1999	Mathew et al.	
	EB	US-5,897,360	04-27-1999	Kawaguchi	
	EC	US-5,900,663	05-04-1999	Johnson et al.	
	ED	US-5,906,680	05-25-1999	Meyerson	
	EE	US-5,917,216	06-29-1999	Floyd et al.	
	EF	US-5,929,481	07-27-1999	Hsieh et al.	
	EG	US-5,943,581	08-24-1999	Lu et al.	
	EH	US-5,949,104	09-07-1999	D'Anna et al.	
	EI	US-5,949,124	09-07-1999	Hadizad et al.	
	EJ	US-5,959,324	09-28-1999	Kohyama	
	EK	US-5,960,271	09-28-1999	Wollesen et al.	
	EL	US-5,972,741	10-26-1999	Kubo et al.	
	EM	US-5,973,360	10-26-1999	Tihanyi	
	EN	US-5,976,936	11-02-1999	Miyajima et al.	
	EO	US-5,981,344	11-09-1999	Hshieh et al.	
	EP	US-5,981,996	11-09-1999	Fujishima	

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A.M.	EQ	US-5,998,833	12-07-1999	Baliga	
	ER	US-6,005,271	12-21-1999	Hshieh	
	ES	US-6,008,097	12-28-1999	Yoon et al.	
	ET	US-6,011,298	01-04-2000	Blanchard	
	EU	US-6,015,727	01-18-2000	Wanlass	
	EV	US-6,020,250	02-01-2000	Kenny et al.	
	EW	US-6,034,415	05-07-2000	Johnson et al.	
	EX	US-6,037,202	03-14-2000	Witek	
	EY	US-6,037,628	03-14-2000	Huang	
	EZ	US-6,037,632	03-14-2000	Omura et al.	
	FA	US-6,040,600	03-21-2000	Uenishi et al.	
	FB	US-6,048,772	04-11-2000	D'Anna	
	FC	US-6,049,108	04-11-2000	Williams et al.	
	FD	US-6,057,558	05-02-2000	Yamamoto et al.	
	FE	US-6,063,678	05-16-2000	D'Anna	
	FF	US-6,064,088	05-16-2000	D'Anna	
	FG	US-6,066,878	05-23-2000	Neilson	
	FH	US-6,081,009	06-27-2000	Neilson	
	FI	US-6,084,264	07-04-2000	Darwish	
	FJ	US-6,084,268	07-04-2000	de Frésart et al.	
	FK	US-6,087,232	07-11-2000	Kim et al.	
	FL	US-6,096,608	08-01-2000	Williams	
	FM	US-6,097,063	08-01-2000	Fujihira	
	FN	US-6,103,578	08-15-2000	Uenishi et al.	
	FO	US-6,104,054	08-15-2000	Corsi et al.	
	FP	US-6,110,799	08-29-2000	Huang	
	FQ	US-6,114,727	09-05-2000	Ogura et al.	
	FR	US-6,137,152	10-24-2000	Wu	
	FS	US-6,156,606	12-05-2000	Michaëlis	
	FT	US-6,156,611	12-05-2000	Lan et al.	
	FU	US-6,163,052	12-19-2000	Liu et al.	
	FV	US-6,165,870	12-26-2000	Shim et al.	
	FW	US-6,168,983	01-02-2001	Rumennik et al.	
	FX	US-6,168,996	01-02-2001	Numazawa et al.	
	FY	US-6,171,935	01-09-2001	Nance et al.	
	FZ	US-6,174,773	01-16-2001	Fujishima	
	GA	US-6,174,785	01-16-2001	Parakh et al.	
	GB	US-6,184,545	02-06-2001	Werner et al.	
	GC	US-6,184,555	02-06-2001	Tihanyi et al.	
	GD	US-6,188,104	02-13-2001	Choi et al.	

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		Number Kind Code ² (if known)			
A. M.	GE	US-6,188,105	02-13-2001	Kocon et al.	
	GF	US-6,190,978	02-20-2001	D'Anna	
	GG	US-6,191,447	02-20-2001	Baliga	
	GH	US-6,198,127	03-06-2001	Kocon	
	GI	US-6,201,279	03-13-2001	Plirsch	
	GJ	US-6,204,097	03-20-2001	Shen et al.	
	GK	US-6,207,994	03-27-2001	Rumennik et al.	
	GL	US-6,222,233	04-24-2001	D'Anna	
	GM	US-6,225,649	05-01-2001	Minato	
	GN	US-6,228,727	05-08-2001	Lim et al.	
	GO	US-6,239,464	05-29-2001	Tsuchitani et al.	
	GP	US-6,265,269	07-24-2001	Chen et al.	
	GQ	US-6,271,100	08-07-2001	Ballantine et al.	
	GR	US-6,271,552	08-07-2001	D'Anna	
	GS	US-6,271,562	08-07-2001	Deboy et al.	
	GT	US-6,274,905	08-14-2001	Mo	
	GU	US-6,277,706	08-21-2001	Ishikawa	
	GV	US-6,285,060	09-04-2001	Korec et al.	
	GW	US-6,291,298	09-18-2001	Williams et al.	
	GX	US-6,291,856	09-18-2001	Miyasaka et al.	
	GY	US-6,294,818	09-25-2001	Fujihira	
	GZ	US-6,297,534	10-02-2001	Kawaguchi et al.	
	HA	US-6,303,969	10-16-2001	Tan	
	HB	US-6,307,246	10-23-2001	Nitta et al.	
	HC	US-6,309,920	10-30-2001	Laska et al.	
	HD	US-6,313,482	11-06-2001	Baliga	
	HE	US-6,326,656	12-04-2001	Tihanyi	
	HF	US-6,337,499	01-08-2002	Werner	
	HG	US-6,346,464	02-12-2002	Takeda et al.	
	HH	US-6,346,469	02-12-2002	Greer	
	HI	US-6,351,018	02-26-2002	Sapp	
	HJ	US-6,353,252	03-05-2002	Yasuhara et al.	
	HK	US-6,359,308	03-19-2002	Hijzen et al.	
	HL	US-6,362,112	03-26-2002	Hamerski	
	HM	US-6,362,505	03-26-2002	Tihanyi	
	HN	US-6,365,462	04-02-2002	Baliga	
	HO	US-6,365,930	04-02-2002	Schillaci et al.	
	HP	US-6,368,920	04-09-2002	Beasom	
	HQ	US-6,368,921	04-09-2002	Hijzen et al.	
	HR	US-6,376,314	04-23-2002	Jerred	

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A. M.	HS	US-6,376,878	04-23-2002	Kocon	
	HT	US-6,376,890	04-23-2002	Tihanyi	
	HU	US-6,384,456	05-07-2002	Tihanyi	
	HV	US-6,388,286	05-14-2002	Baliga	
	HW	US-6,388,287	05-14-2002	Deboy et al.	
	HX	US-6,400,003	06-04-2002	Huang	
	HY	US-6,429,481 B1	08-06-2002	Mo et al.	
	HZ	US-6,433,385	08-13-2002	Kocon et al.	
	IA	US-6,436,779	08-20-2002	Hurkx et al.	
	IB	US-6,437,399	08-20-2002	Huang	
	IC	US-6,441,454	08-27-2002	Hijzen et al.	
	ID	US-6,452,230	09-17-2002	Boden, Jr.	
	IE	US-6,465,304	10-15-2002	Blanchard et al.	
	IF	US-6,465,843	10-15-2002	Hirler et al.	
	IG	US-6,465,869	10-15-2002	Ahters et al.	
	IH	US-6,472,678	10-29-2002	Hshieh et al.	
	II	US-6,472,708	10-29-2002	Hshieh et al.	
	IJ	US-6,475,884	11-05-2002	Hshieh et al.	
	IK	US-6,476,443	11-05-2002	Kinzer	
	IL	US-6,479,352	11-12-2002	Blanchard	
	IM	US-6,489,652 B1	12-03-2002	Jeon et al.	
	IN	US-6,501,146	12-31-2002	Harada	
	IO	US-2001/0023961 A1	09-27-2001	Hsieh et al.	
	IP	US-2001/0028083 A1	10-11-2001	Onishi et al.	
	IQ	US-2001/0032998 A1	10-25-2001	Iwamoto et al.	
	IR	US-2001/0041400 A1	11-15-2001	Ren et al.	
	IS	US-2001/0049167 A1	12-06-2001	Madson	
	IT	US-2001/0050394 A1	12-13-2001	Onishi et al.	
	IU	US-2002/0009832 A1	01-24-2002	Blanchard	
	IV	US-2002/0014658 A1	02-07-2002	Blanchard	
	IW	US-2002/0066924 A1	06-06-2002	Blanchard	
	IX	US-2002/0070418 A1	06-13-2002	Kinzer et al.	
	IY	US-2003/0060013 A1	03-27-2003	Marchant	
	IZ	US-2003/0100933	08-01-2002	Marchant	
	JA	US-2003/0100933 A1	08-01-2002	Marchant	
	JB	US-2003/0193067 A1	10-16-2003	Kim	

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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
A.M	JC	DE ✓	4300806	C1	12-23-1993	Siemens AG		<input checked="" type="checkbox"/>
	JD	DE ✓	19736981	A1	08-20-1998	Mitsubishi Denki		<input checked="" type="checkbox"/>
	JE	EP ✓	0747967	B1	02-27-2002	ST Microelectronics Inc.		<input type="checkbox"/>
	JF	EP ✓	0975024	A2	01-02-2000	Fuji Electric Co. LTD.		<input type="checkbox"/>
	JG	EP ✓	1026749	A1	08-09-2000	Mitsubishi Denki Kabushiki		<input type="checkbox"/>
	JH	EP ✓	1054451	A2	11-22-2000	Intersil Corporation		<input type="checkbox"/>
	JI	EP ✓	1205980	A1	05-15-2002	Infineon Technologies AG		<input type="checkbox"/>
	JJ	JP ✓	01-192174	A	08-02-1989	Hitachi LTD.		<input checked="" type="checkbox"/>
	JK	JP ✓	05226638	A	09-03-1993	Wakatabe et al.		<input checked="" type="checkbox"/>
	JL	JP ✓	2000-040822		02-08-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	JM	JP ✓	2000-040872		02-08-2000	Senju Metal IND CO LTD.		<input checked="" type="checkbox"/>
	JN	JP ✓	2000-156978	A	06-06-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	JO	JP ✓	2000-277726	A	10-06-2000	Toshiba Corp.		<input checked="" type="checkbox"/>
	JP	JP ✓	2000-277728	A	10-06-2000	NEC Kansai LTD.		<input checked="" type="checkbox"/>
	JQ	JP ✓	2001-015448		01-19-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	JR	JP ✓	2001-015752		01-19-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	JS	JP ✓	2001-102577	A	04-13-2001	Toshiba Corp.		<input checked="" type="checkbox"/>
	JT	JP ✓	2001-111041	A	02-20-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	JU	JP ✓	2001-135819	A	05-18-2001	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	JV	JP ✓	2001-144292	A	05-25-2001	Denso Corp.		<input checked="" type="checkbox"/>
	JW	JP ✓	2001-244461	A	09-07-2001	Toyota Central Res & Dev Lab INC.		<input checked="" type="checkbox"/>
	JX	JP ✓	2001-313391	A	11-09-2001	S. Takahiro et al.		<input checked="" type="checkbox"/>
	JY	JP ✓	2002-083976	A	03-22-2002	Naito et al.		<input checked="" type="checkbox"/>
	JZ	JP ✓	62-069562		03-30-1987	Mitsubishi Electric Corp		<input checked="" type="checkbox"/>
	KA	JP ✓	63-186475		08-02-1988	Nissan Motor Co. LTD.		<input checked="" type="checkbox"/>
	KB	JP ✓	63-288047		11-25-1988	Toshiba Corp.		<input checked="" type="checkbox"/>
	KC	JP ✓	64-022051		01-25-1989	Matsushita Electric Ind		<input checked="" type="checkbox"/>
	KD	PCT ✓	WO 00/33386	A2	06-08-2000	Koninklijke Philips Electronics		<input type="checkbox"/>
	KE	PCT ✓	WO 00/68997	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	KF	PCT ✓	WO 00/68998	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	KG	PCT ✓	WO 00/75965	A2	12-14-2000	General Semiconductor, Inc.		<input type="checkbox"/>
	KH	PCT ✓	WO 01/06550	A1	01-23-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	KI	PCT ✓	WO 01/06557	A1	01-25-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	KJ	PCT ✓	WO 01/45155	A1	06-21-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	KK	PCT ✓	WO 01/59847	A2	08-16-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	KL	PCT ✓	WO 01/71815		09-27-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	KM	PCT ✓	WO 01/95385	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>

Examiner Signature	ANH D. MAI	Date Considered	10/17/2005
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	10/801,499
				Filing Date	March 15, 2004
				First Named Inventor	Calafut, Daniel
				Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned				
Sheet	8	of	11	Attorney Docket Number	018865-015200US

FOREIGN PATENT DOCUMENTS								
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
A.M.	KN	PCT ✓	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>
I	KO	PCT ✓	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation		<input type="checkbox"/>
	KP	PCT ✓	WO 02/047171	A1	06-13-2002	International Rectifier Corporation		<input type="checkbox"/>
								<input type="checkbox"/>

Examiner Signature	ANH D. MA	Date Considered	10/17/2005
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A. U.	KQ ✓	BAI et al., "Novel automated optimization of power MOSFET for 12V input, high-frequency DC-DC converter," <i>International Symposium on Power Semiconductors and ICs, Technical Digest</i> , (2003), pp. 366-369.	
	KR ✓	BALIGA "New Concepts in Power Rectifiers," <i>Physics of Semiconductor Devices, Proceedings of the Third Int'l Workshop, Madras (India), Committee on Science and Technology in Developing Countries</i> (1985), pp. 471-481.	
	KS ✓	BALIGA "Options for CVD of Dielectrics Include Low-k Materials," <i>Technical Literature from Semiconductor International</i> , June 1998, 4 pages total.	
	KT ✓	BALIGA, et al., "Improving the reverse recovery of power MOSFET integral diodes by electron irradiation," (December 1983) <i>Solid State Electronics</i> , Vol. 26, No. 12, pp. 1133-1141.	
	KU ✓	BROWN et al. Novel Trench Gate Structure Developments Set the Benchmark for Next Generation Power MOSFET Switching Performance. <i>Power Electronics - May 2003 Proceedings (PCIM)</i> , Nuremberg, Vol. 47, pp. 275-278.	
	KV ✓	BULUCEA "Trench DMOS Transistor Technology For High Current (100 A Range) Switching" <i>Solid-State Electronics Vol.34 No. pp.493-507</i> (1991).	
	KW ✓	CHANG et al. "Numerical and experimental Analysis of 500-V Power DMOSFET with an Atomic-Lattice Layout," <i>IEEE Transactions on Electron Devices</i> 36:2623 (1989).	
	KX ✓	CHANG et al. "Self-Aligned UMOSFET's with a Specific On-Resistance of 1mΩ cm ² ," <i>IEEE Transactions on Electron Devices</i> 34:2329-2334 (1987).	
	KY ✓	CHENG, et al., "Fast reverse recovery body diode in high-voltage VDMOSFET using cell-distributed schottky contacts," (May 2003) <i>IEEE Transactions on Electron Devices</i> , Vol. 50, No. 5, pp. 1422-1425.	
	KZ ✓	"CoolMOS™ the second generation," <i>Infineon Technologies product information</i> , (2000), 2 pages total.	
	LA ✓	CURTIS, et al. "APCVD TEOS: 03 Advanced Trench Isolation Applications," <i>Semiconductor Fabtech 9th Edition</i> (1999) 8 pages total.	
	LB ✓	DARWISH et al. A New Power W-Gated Trench MOSFET (WMOSFET) with High Switching Performance. <i>ISPSD Proceedings - April 2003, Cambridge</i> , 4 pages total.	
	LC ✓	DJEKIC, O. et al., "High frequency synchronous buck converter for low voltage applications," (1998) <i>Proc. IEEE Power Electronics Specialist Conf. (PESC)</i> , pp. 1248-1254.	
	LD ✓	FUJIHIRA "Theory of Semiconductor Superjunction Devices" <i>Jpn. J. Appl. Phys. Vol 36 pp. 6254-6262</i> (1997).	
	LE ✓	GAN et al. "Poly Flanked VDMOS (PFVDMOS): A Superior Technology for Superjunction Devices," <i>IEEE Power Electronics Specialists Conference</i> , 17-22 June 2001, Vancouver, Canada (2001), 4 pages total.	
	LF ✓	GLENN et al. "A Novel Vertical Deep Trench RESURF DMOS (VTR-DMOS)" <i>IEEE ISPD 2000</i> , May 22-25, Toulouse France, pp. 197-200.	

Examiner Signature	ANDY D. MAI	Date Considered	10/17/2005
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A.M.	LG ✓	"IR develops CoolMOS™ -equivalent technology, positions it at the top of a 3-tiered line of new products for SMPS," International Rectifiers company information available at http://www.irf.com (1999) 3 pages total.	
	LH ✓	KAO et al. "Two Dimensional Thermal Oxidation of Silicon-I. Experiments," <u>IEEE Transactions on Electron Devices</u> , Vol. ED-34, No. 5, May 1987, pp. 1008-1017.	
	LI ✓	KAO et al., "TWO DIMENSIONAL THERMAL OXIDATION OF SILICON-II. MODELING STRESS EFFECTS IN WET OXIDES," <u>IEEE TRANSACTIONS ON ELECTRON DEVICES</u> , VOL. ED-35, NO. 1, JANUARY 1988, pp. 25-37.	
	LJ ✓	KASSAKIAN, J.G. et al., "High-frequency high-density converters for distributed power supply systems," (April 1988) <i>Proceedings of the IEEE</i> , Vol. 76, No. 4, pp. 362-376.	
	LK ✓	KORMAN, C.S. et al., "High performance power DMOSFET with integrated schottky diode," (1989) <i>Proc. IEEE Power Electronics Specialist Conf. (PESC)</i> , pp. 176-179.	
	LL ✓	LORENZ et al. "COOL MOS- An important milestone towards a new power MOSFET generation" <i>Power Conversion</i> pp. 151-160 (1988).	
	LM ✓	MAKSIMOVIC, A.M. et al., "Modeling and simulation of power electronic converters," (June 2001) <i>Proceedings of the IEEE</i> , Vol. 89, No. 6, pp. 898-912.	
	LN ✓	MEHROTRA, M. et al., "Very low forward drop JBS rectifiers fabricated using submicron technology," (November 1993) <i>IEEE Transactions on Electron Devices</i> , Vol. 40, No. 11, pp. 2131-2132.	
	LO ✓	MOGHADAM "Delivering Value Around New Industry Paradigms," <i>Technical Literature from Applied Materials</i> , pages 1-11, Volume 1, Issue 2, November 1999.	
	LP ✓	PARK et al., "Lateral Trench Gate Super-Junction SOI-LDMOSFETs with Low On-Resistance," <i>Institute for Microelectronics, University of Technology Vienna, Austria</i> (2002), pp. 283-285.	
	LQ ✓	SAKAI et al., "Experimental investigation of dependence of electrical characteristics of device parameters in trench MOS barrier, schottky diodes," (1998) <i>International Symposium on Power Semiconductors and ICs, Technical Digest</i> , pp. 293-296.	
	LR ✓	SHENAI et al., "Current transport mechanisms in atomically abrupt metal-semiconductor interfaces," (April 1988) <i>IEEE Transactions on Electron Devices</i> , Vol. 35, No. 4, pp. 468-482.	
	LS ✓	SHENAI et al., "Monolithically integrated power MOSFET and schottky diode with improved reverse recovery characteristics," (April 1990) <i>IEEE Transactions on Electron Devices</i> , Vol. 37, No. 4, pp. 1167-1169.	
	LT ✓	SHENOY et al. "Analysis of the Effect of Charge Imbalance on the Static and Dynamic Characteristic of the Super Junction MOSFET," <i>IEEE International Symposium on Power Semiconductor Devices</i> 1999, pp. 99-102 (1999).	
	LU ✓	SINGER "Empty Spaces In Silicon (ESS): An Alternative to SOI," <i>Semiconductor International</i> page 42, December 1999.	

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A.M.	LV ✓	TABISZ, et al., "A MOSFET resonant synchronous rectifier for high-frequency dc/dc converters," (1990) <i>Proc. IEEE Power Electronics Specialist Conf. (PESC)</i> , pp. 769-779.	
	LW ✓	Technical Literature from Quester Technology, Model APT-4300 300mm Atmospheric TEOS/Ozone CVD System (unknown date), 3 pages total.	
	LX ✓	Technical Literature from Quester Technology, Model APT-6000 Atmospheric TEOS-Ozone CVD System (unknown date), 2 pages total.	
	LY ✓	Technical Literature from Silicon Valley Group Thermal Systems, APNext, High Throughput APCVD Cluster Tool for 200 mm/300 mm Wafer Processing (unknown date), 2 pages total.	
	LZ ✓	TU, et al. "On the reverse blocking characteristics of schottky power diodes," (December 1992) <i>IEEE Transactions on Electron Devices</i> . Vol. 39, No. 12, pp. 2813-2814 2 pages total.	
	MA ✓	UEDA et al. "An Ultra-Low On-Resistance Power MOSFET Fabricated by Using a Fully Self-Aligned Process," <i>IEEE Transactions on Electron Devices</i> 34:926-930 (1987).	
	MB ✓	WILAMOWSKI "Schottky Diodes with High Breakdown Voltages," <i>Solid-State Electronics</i> 26:491-493 (1983).	
	MC ✓	WOLF, "Silicon Processing for The VLSI Era" Vol. 2 Process Integration Lattice Press (1990) 3 pages total.	
	MD ✓	YAMASHITA, et al., "Conduction Power loss in MOSFET synchronous rectifier with parallel-connected schottky barrier diode, (July 1998) <i>IEEE Transactions on Power electronics</i> , Vol. 13, No. 4, pp. 667-673.	

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